



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub> max       | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|----------------------|-------------------------------|--|
| 30V                  | 1.5Ω @ V <sub>GS</sub> = 4.5V |  |
|                      | 2.0Ω @ V <sub>GS</sub> = 2.5V | 0.224  |
|                      | 3.0Ω @ V <sub>GS</sub> = 1.8V | 0.22A  |
|                      | 4.5Ω @ V <sub>GS</sub> = 1.5V |  |

### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- General Purpose Interfacing Switch
- **Power Management Functions**
- Analog Switch

### **Features and Benefits**

- Low Package Profile, 0.42mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

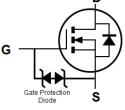
- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (approximate)

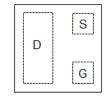




**Bottom View** 







**Equivalent Circuit** 

Top View Package Pin Configuration

## Ordering Information (Note 4)

| Part Number   | Case         | Packaging       |  |
|---------------|--------------|-----------------|--|
| DMN31D5UFZ-7B | X2-DFN0606-3 | 10K/Tape & Reel |  |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



R6 = Product Type Marking Code

Top View Bar Denotes Gate and Source Side



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                    |                  |  | Symbol          | Value      | Units |
|-----------------------------------|------------------|--|-----------------|------------|-------|
| Drain-Source Voltage              |                  |  | $V_{DSS}$       | 30         | V     |
| Gate-Source Voltage               | V <sub>GSS</sub> | ±12  | V               |            |       |
| Continuous Drain Current (Note 5) | Steady<br>State  | $T_A = +25^{\circ}C$<br>$T_A = +85^{\circ}C$ | I <sub>D</sub>  | 220<br>150 | mA    |
| Pulsed Drain Current (Note 6)     |                  |  | I <sub>DM</sub> | 500        | mA    |

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol       | Value                            | Units       |      |
|--|--------------|----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | Steady state | $P_{D}$                          | 393         | mW   |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state | $R_{\theta JA}$                  | 318         | °C/W |
| Operating and Storage Temperature Range          |              | T <sub>J,</sub> T <sub>STG</sub> | -55 to +150 | °C   |

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

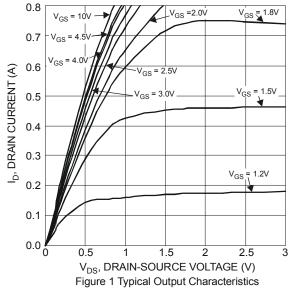
|   |                     |     |      | I   |      |  |  |
|---|---------------------|-----|------|-----|------|--|--|
| Characteristic  | Symbol              | Min | Тур  | Max | Unit | Test Condition   |  |
| OFF CHARACTERISTICS (Note 7)                            |                     |     |      |     |      |  |  |
| Drain-Source Breakdown Voltage                          | BV <sub>DSS</sub>   | 30  | 1    | _   | V    | $V_{GS} = 0V, I_D = 250\mu A$                              |  |
| Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C | I <sub>DSS</sub>    | _   | 1    | 100 | nA   | V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V                |  |
| Gate-Source Leakage                                     | I <sub>GSS</sub>    | _   |      | ±10 | μA   | $V_{GS}$ = ±10V, $V_{DS}$ = 0V                             |  |
| ON CHARACTERISTICS (Note 7)                             |                     |     |      |     |      |  |  |
| Gate Threshold Voltage                                  | V <sub>GS(th)</sub> | 0.4 | -    | 1.0 | V    | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                       |  |
|   |                     | _   | 1    | 1.5 |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA             |  |
|   |                     | _   | 1    | 2.0 |      | $V_{GS} = 2.5V, I_D = 50mA$                                |  |
| Static Drain-Source On-Resistance                       | R <sub>DS(ON)</sub> | _   | 1    | 3.0 | Ω    | $V_{GS} = 1.8V, I_D = 20mA$                                |  |
|   |                     | _   | 1    | 4.5 |      | V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA              |  |
|   |                     | _   | 2.8  | _   |      | V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 1mA               |  |
| Diode Forward Voltage                                   | $V_{SD}$            | _   | 0.75 | 1.0 | V    | $V_{GS} = 0V$ , $I_S = 10mA$                               |  |
| DYNAMIC CHARACTERISTICS (Note 8)                        |                     |     |      |     |      |  |  |
| Input Capacitance                                       | C <sub>iss</sub>    | _   | 22.2 | _   | pF   |  |  |
| Output Capacitance                                      | Coss                | _   | 2.9  | _   | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz |  |
| Reverse Transfer Capacitance                            | C <sub>rss</sub>    | _   | 2.2  | _   | pF   | 1 - 1.0WHZ   |  |
| Total Gate Charge                                       | Qg                  | _   | 0.35 | _   | nC   | V 45V V 45V  |  |
| Gate-Source Charge                                      | $Q_{gs}$            | _   | 0.05 | _   | nC   | $V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 200 \text{mA}$     |  |
| Gate-Drain Charge                                       | $Q_{gd}$            | _   | 0.02 | _   | nC   | - ID - 200IIIA   |  |
| Turn-On Delay Time                                      | t <sub>D(on)</sub>  | _   | 3.1  | _   | ns   |  |  |
| Turn-On Rise Time                                       | t <sub>r</sub>      | _   | 2.0  | _   | ns   | $V_{DD} = 10V, V_{GS} = 4.5V,$                             |  |
| Turn-Off Delay Time                                     | t <sub>D(off)</sub> | _   | 20   | _   | ns   | $R_G = 6\Omega$ , $I_D = 200 \text{mA}$                    |  |
| Turn-Off Fall Time                                      | t <sub>f</sub>      | _   | 6.9  | _   | ns   |  |  |

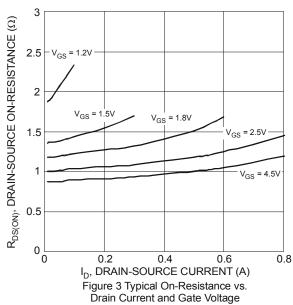
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.







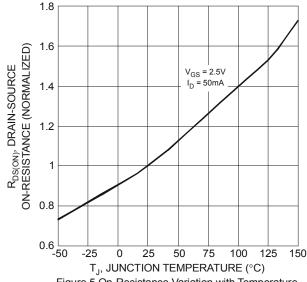
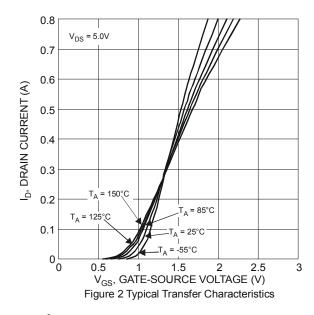
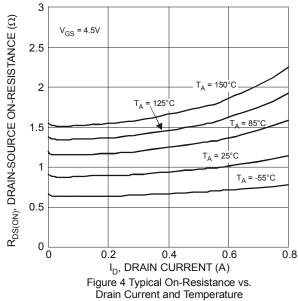


Figure 5 On-Resistance Variation with Temperature





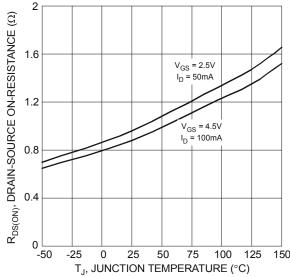


Figure 6 On-Resistance Variation with Temperature





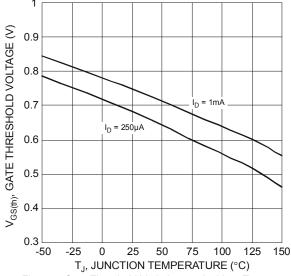
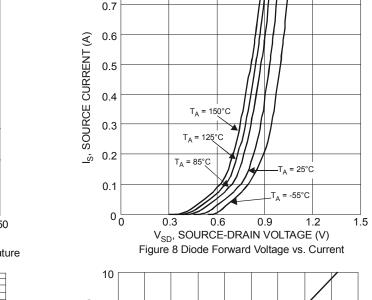
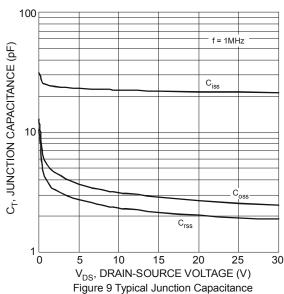
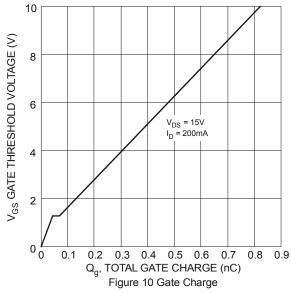


Figure 7 Gate Threshold Variation vs. Ambient Temperature



0.8





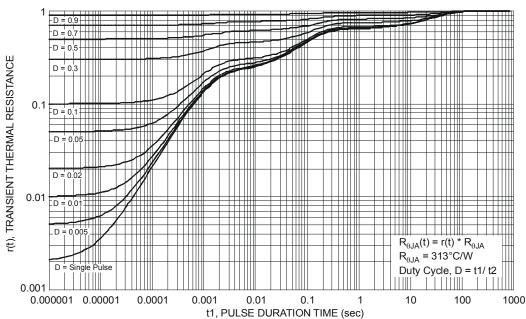
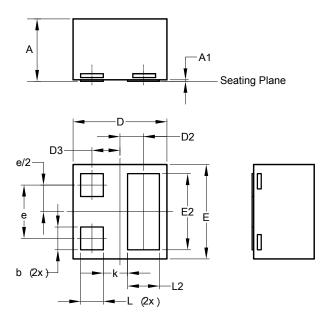


Figure 11 Transient Thermal Resistance



# **Package Outline Dimensions**

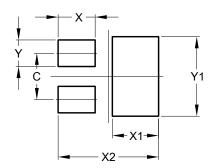
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| X2-DFN0606-3         |           |           |      |  |  |
|----------------------|-----------|-----------|------|--|--|
| Dim                  | Min       | Тур       |      |  |  |
| Α                    | 0.36      | 0.42      | 0.39 |  |  |
| A1                   | 0         | 0.05      | 0.02 |  |  |
| b                    | 0.10      | 0.20      | 0.15 |  |  |
| D                    | 0.57      | 0.67      | 0.62 |  |  |
| D2                   | 0.155 BSC |           |      |  |  |
| D3                   | C         | 0.185 BSC |      |  |  |
| Е                    | 0.57      | 0.57 0.67 |      |  |  |
| E2                   | 0.40      | 0.60      | 0.50 |  |  |
| е                    | 0.35 BSC  |           |      |  |  |
| k                    | 0.16 REF  |           |      |  |  |
| Ĺ                    | 0.09      | 0.21      | 0.15 |  |  |
| L2                   | 0.11      | 0.31      | 0.21 |  |  |
| All Dimensions in mm |           |           |      |  |  |

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions   | Value   |  |  |
|--------------|---------|--|--|
| Difficusions | (in mm) |  |  |
| С            | 0.350   |  |  |
| Х            | 0.280   |  |  |
| X1           | 0.350   |  |  |
| X2           | 0.760   |  |  |
| Y            | 0.200   |  |  |
| Y1           | 0.600   |  |  |



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